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SINGLE CHIP BATTERY PROTECTION SOLUTION FOR 1-CELL Li+ BATTERY PACK

Description

The DIODES[™] AP9221 is a single-chip protection solution specially designed for 1-cell Li+ rechargeable battery pack applications.

The AP9221 includes a 1-cell Lithium ion battery protection chip and dual N-CH MOSFET with common drain.

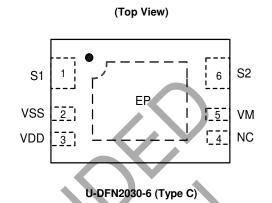
The AP9221 provides rich battery protection features and can turn-off the N-CH MOSFET by detecting overcharge voltage/current, overdischarge voltage/current, or load short circuit. The AP9221 has built-in fixed delay time to save external components.

The AP9221 is available in the U-DFN2030-6 (Type C) package.

Features

- High Voltage CMOS Process, Up to 24V (VDD to VM)
- Low Quiescent Current (+25°C)
- In Normal Mode, 3.0µA (Typ.), 4.5µA (Max.) V_{DD} = 3.5V
- In Power-Down Mode, 0.1µA (Max.)
- High-Accuracy Voltage Detection Circuit (+25°C)
- Overcharge Detection Voltage: 3.5V to 4.5V (5mV Steps) Accuracy-15mV, +25mV
- Overcharge Hysteresis Voltage Range: 0.1V to 0.4V (50mV Steps) Accuracy ±50mV
- Overdischarge Detection Voltage: 2.0V to 3.4V (10mV Steps) Accuracy ±35mV
- Overdischarge Hysteresis Voltage Range: 0V to 0.7V (40mV Steps) Accuracy ±65mV
- Discharge Overcurrent Detection Voltage: 0.025V to 0.2V (10mV Steps) Accuracy ±12mV
- Short Current Detection Voltage: 0.12V to 0.45V (50mV Steps) Accuracy ±50mV
- Charge Overcurrent Detection Voltage: -0.2V to -0.025V (10mV Steps) Accuracy ±12mV
- Overcharger Detection Voltage: 8.0V (Fixed) Accuracy ±2V
- Overcharger Release Voltage: 7.3V (Fixed) Accuracy ±2V
- Built-In Fixed Detection Delay Time (+25°C), Accuracy ±20%
- Power-Down Mode Selectable (Yes or No)
- 0V Battery Charge Selectable (Permission or Inhibition)
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>
- Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Pin Assignments

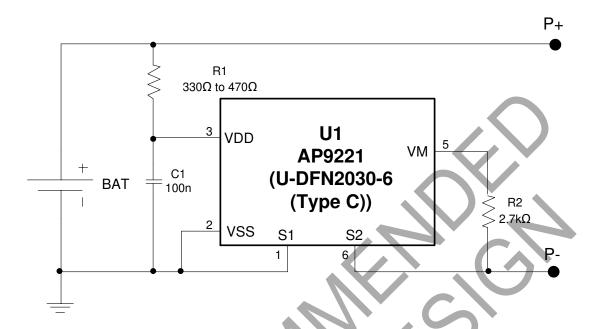


Applications

Li+ rechargeable battery packs



Typical Applications Circuit (Note 4)



Note: 4. R1 and C1 are used to stabilize the supply voltage of the AP9221. The recommended range of the R1 value is 330Ω to 470Ω and C1 value is 10nF to 1000nF, typical value is 100nF. R2 should be connected between P- to VM sense terminal to monitor the status of charger and the charge/discharge current. The R2 should be between 300Ω and 4kΩ, typical value is 2.7kΩ. R1 and R2 are also used as current limit resistors if the battery or charger is connected reversely. Polarity reversing may cause the power consumption of R1 and R2 to go over their power dissipation rating, therefore R1 and R2 values should be selected appropriately for the actual application. If R2 is more than 4kΩ resistor, charge may not be off due to the voltage drop on R2.

For power down mode, when first connecting AP9221 system board to the battery, it is necessary to use charger or to short P- to the battery negative polarity. Once the AP9221 is activated, the charger or connection can be removed, otherwise the battery cannot discharge current through system board.

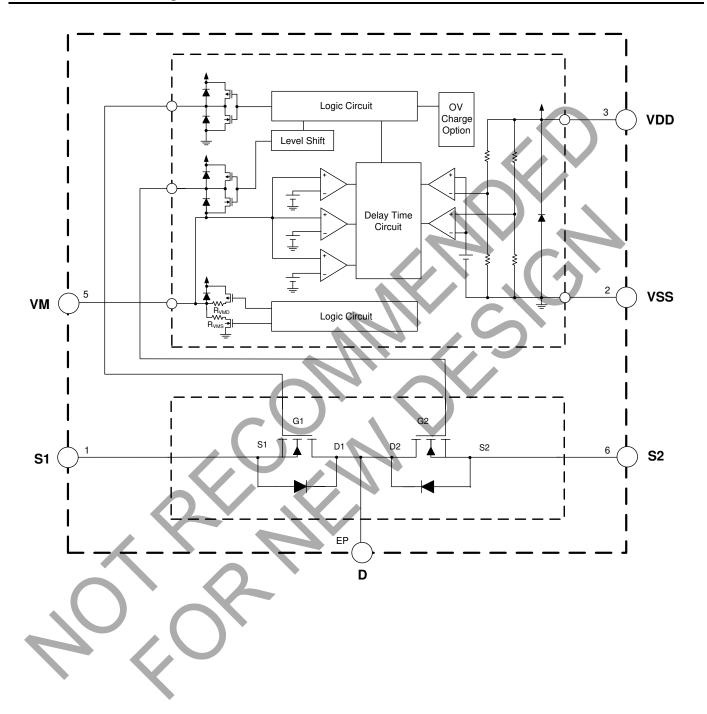
The values selected should follow the recommended typical range mentioned above. It has not been confirmed whether the operation is normal or not in circuits other than the above example of connection. In addition, the example of connection shown above and the typical value do not exactly guarantee proper operation. Please perform the actual application to set the suitable value through your complete evaluation.

Pin Number	Pin Name	Function
1	S1	Source pin of discharging MOSFET, connecting this pin to battery negative pole.
2	VSS	Negative power supply pin
3	VDD	Positive power supply pin, connecting this pin to battery positive pole through R1
4	NC	Not connected, leave this pin floating
5	VM	Charger negative input pin, short this pin to S2 pin through R2
6	S2	Source pin of charging MOSFET, connecting this pin to charge negative input.
EP	D	Thermal PAD is common drain of charge and discharge MOSFET, so in PCB layout, prefer to use large copper area to cover this pad for better thermal dissipation, then leave it open.

Pin Descriptions



Functional Block Diagram





Absolute Maximum Ratings (Notes 5 & 6)

Symbol	Parameter	Rating	Unit
VDD	Supply Voltage (Between VDD and VSS)	-0.3 to 12	V
V _{DM}	Charge Input Voltage (Between VDD and VM for Protection Chip)	-0.3 to 24	V
VDSS	MOSFET Drain-to-Source Voltage	20	V
Vgss	MOSFET Gate-to-Source Voltage	±12	V
1-	Continuous Drain Current, $V_{GS} = 4.5V$, $T_A = +25^{\circ}C$	2.8	А
ID	Continuous Drain Current, $V_{GS} = 4.5V$, $T_A = +70^{\circ}C$	2.2	А
PD	Power Dissipation	1,000	mW
TJ	Maximum Junction Temperature	+150	°C
Tstg	Storage Temperature Range	-65 to +150	°C
_	ESD (Charged-Device Model)	1,000	V
_	ESD (Human Body Model)	2,000	V

Notes: 5. Stresses beyond those listed under *Absolute Maximum Ratings* can cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods can affect device reliability.

 Ratings apply to ambient temperature at +25°C. The JEDEC High-K board design used to derive this data was a 2 inch × 2 inch multilayer board with 2 ounce internal power and ground planes and 2-ounce copper traces on the top and bottom of the board.

Recommended Operating Conditions

Symbol	Parameter	Min	Мах	Unit
V _{DD}	Supply Voltage (Between VDD and VSS)	1.5	5.5	V
V _{DM}	Charge Input Voltage (Between VDD and VM)	-0.3	5.5	V
Та	Operating Ambient Temperature	-40	+85	°C



Symbol	Parameter	Condition	Min	Тур	Max	Unit
Vcu	Overcharge Detection Voltage	V _M = 0V	V _{CU} - 0.015	Vcu	V _{CU} + 0.025	V
M	Oversharra Delagos Maltara	$V_{CL} eq V_{CU}$	V _{CL} - 0.050	V _{CL}	V _{CL} + 0.050	V
Vcl	Overcharge Release Voltage	Vcl = Vcu	V _{CL} - 0.015	V _{CL}	V _{CL} + 0.025	V
VDL	Overdischarge Detection Voltage	V _M = 0V	V _{DL} - 0.035	VDL	V _{DL} + 0.035	V
M	Quardiasharra Dalasas Valtaga	$V_{DU} \neq V_{DL}$	V _{DU} - 0.065	Vdu	V _{DU} + 0.065	V
V _{DU}	Overdischarge Release Voltage	Vdu = Vdl	V _{DU} - 0.035	VDU	V _{DU} + 0.035	V
VDOC	Discharge Overcurrent Detection Voltage	Vdd = 3.5V	V _{DOC} -0.012	VDOC	V _{DOC} +0.012	V
VSHORT	Load Short-Circuiting Detection Voltage	Vdd = 3.5V	VSHORT -0.050	VSHORT	Vshort +0.050	V
Vcoc	Charge Overcurrent Detection Voltage	Vdd = 3.5V	Vcoc -0.012	Vcoc	Vcoc +0.012	V
cc (Power D	Down Function)					
lcc	Current Consumption During Operation	Vdd = 3.5V, Vm = 0V	G	3.0	4.5	μA
IPDN	Current Consumption During Power-Down Mode	V _{DD} = 1.8V, VM Pin Floating		—	0.1	μA
c (Auto-W	ake Up Function)					
Icc	Current Consumption During Operation	$V_{DD} = 3.5V, V_M = 0V$	-	3	4.5	μA
Ιαυτο	Current Consumption During Auto-Wake Mode	V _{DD} = 1.8V, VM Pin Floating		3.5	5.5	μA
Rvmd	Resistance Between VM Pin and VDD Pin	V _{DD} = 1.8V, V _M = 0V	150	300	500	kΩ
Rvms	Resistance Between VM Pin and VSS Pin	$V_{DD} = 3.5V, V_M = 1.0V$	10	30	50	kΩ
V _{0CHA}	0V Battery Charge Starting Charge Voltage	0V Battery Charging "Available"	1.2	_		V
V _{0INH}	0V Battery Charge Inhibition Battery Voltage	0V Battery Charging "Unavailable"	_	—	0.45	V
Vovchg	Overvoltage Charge Detection Voltage	V _{DD} = 3.5V	6.0	8.0	10.0	V
VOVCHGR	Overvoltage Charge Release Voltage	V _{DD} = 3.5V	5.3	7.3	9.3	V
tcu	Overcharge Detection Delay Time	V _{DD} = 3.6 to 4.5V	800	1000	1200	ms
tcur	Overcharge Release Delay Time	$V_{M} = 0V$	1.6	2	2.4	ms
tDL	Overdischarge Detection Delay Time	V _{DD} = 3.6V to 2.0V	92	115	138	ms
tdlr	Overdischarge Release Delay Time	$V_{M} = 0V$	1.6	2	2.4	ms
tDOC	Discharge Overcurrent Detection Delay Time	Vdd = 3.6V	8	10	12	ms
t DOCR	Discharge Overcurrent Release Delay Time	V _M = 0V	1.6	2	2.4	ms
t SHORT	Load Short Detection Delay Time	V _{DD} = 3.6V	288	360	432	μs
tcoc	Charge Overcurrent Detection Delay Time	VDD = 3.6V	8	10	12	ms
tcocr	Charge Overcurrent Release Delay Time	$V_{M} = 0V$	1.6	2	2.4	ms

$\label{eq:Electrical Characteristics} (T_{A} = +25^{\circ}C, V_{DD} = 3.5V, V_{SS} = 0V, R1 = 220\Omega, R2 = 1.0k\Omega, C1 = 100nF, unless otherwise specified.)$



Electrical Characteristics (continued) (T_A = -40°C to +85°C, V_{DD} = 3.5V, V_{SS} = 0V, R1 = 220 Ω , R2 = 1.0k Ω , C1 = 100nF, unless otherwise specified.)

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
Vcu	Overcharge Detection Voltage	$V_{M} = 0V$	V _{CU} - 0.050	Vcu	V _{CU} + 0.040	V
	Ourseland Dalassa Malland	$V_{CL} eq V_{CU}$	V _{CL} - 0.070	V _{CL}	V _{CL} + 0.060	V
V _{CL}	Overcharge Release Voltage	V _{CL} = V _{CU}	V _{CL} - 0.050	VCL	V _{CL} + 0.040	V
VDL	Overdischarge Detection Voltage	V _M = 0V	V _{DL} - 0.080	VDL	V _{DL} + 0.080	V
		$V_{DU} eq V_{DL}$	V _{DU} - 0.150	VDU	V _{DU} + 0.190	V
Vdu	Overdischarge Release Voltage	VDU = VDL	V _{DU} - 0.080	VDU	V _{DU} + 0.080	V
VDOC	Discharge Overcurrent Detection Voltage	VDD = 3.5V	VDOC -0.030	VDOC	V _{DOC} +0.030	V
VSHORT	Load Short-Circuiting Detection Voltage	VDD = 3.5V	VSHORT -0.10	VSHORT	VSHORT +0.10	V
V _{COC}	Charge Overcurrent Detection Voltage	V _{DD} = 3.5V	Vcoc -0.040	Vcoc	Vcoc +0.040	V
Icc (Power-I	Down Function)				101010	
Icc	Current Consumption During Operation	Vdd = 3.5V, Vm = 0V	5	3.0	7.0	μΑ
I _{PDN}	Current Consumption During Power-Down Mode	V _{DD} = 1.8V, VM Pin Floating		_	1.0	μA
I _{CC} (Auto-Wa	ake Up Function)					
lcc	Current Consumption During Operation	Vdd = 3.5V, Vm = 0V	_	3	4.5	μΑ
Ιαυτο	Current Consumption During Auto-Wake Mode	V _{DD} = 1.8V, VM Pin Floating	_	6	8	μΑ
RVMD	Resistance between VM Pin and VDD Pin	$V_{DD} = 1.8V, V_{M} = 0V$	100	300	650	kΩ
R _{VMS}	Resistance between VM Pin and VSS Pin	$V_{DD} = 3.5V, V_M = 1.0V$	5	30	65	kΩ
Vocha	0V Battery Charge Starting Charge Voltage	0V Battery Charging "Available"	1.2	—	—	V
VOINH	0V Battery Charge Inhibition Battery Voltage	0V Battery Charging "Unavailable"	—	_	0.3	V
Vovchg	Overvoltage Charge Detection Voltage	V _{DD} = 3.5V	5.5	8.0	10.5	V
Vovchgr	Overvoltage Charge Release Voltage	V _{DD} = 3.5V	5.0	7.3	9.5	V
tcu	Overcharge Detection Delay Time	V _{DD} = 3.6V to 4.5V	600	1000	1400	ms
tcur	Overcharge Release Delay Time	$V_{M} = 0V$	1.2	2	2.8	ms
tDL	Overdischarge Detection Delay Time	V _{DD} = 3.6V to 2.0V	69	115	161	ms
tdlr	Overdischarge Release Delay Time	$V_{M} = 0V$	1.2	2	2.8	ms
tDOC	Discharge Overcurrent Detection Delay Time	V _{DD} = 3.6V	6	10	14	ms
t DOCR	Discharge Overcurrent Release Delay Time	$V_{M} = 0V$	1.2	2	2.8	ms
t SHORT	Load Short Detection Delay Time	Vdd = 3.6V	216	360	504	μs
tcoc	Charge Overcurrent Detection Delay Time	Vdd = 3.6V	6	10	14	ms
tcocr	Charge Overcurrent Release Delay Time	V _M = 0V	1.2	2	2.8	ms



Electrical Characteristics (continued) (Notes 7 & 8) ($T_A = +25^{\circ}C$, $V_{DD} = 3.5V$, $V_{SS} = 0V$, $R1 = 220\Omega$, $R2 = 1.0k\Omega$, C1 = 100nF, unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 20V, V_{GS} = 0$	—	—	1.0	μA
Rss(ON)1	Static Source-Source On-Resistance 1	V _{DD} = 4.5V, I _D = 1A	_	130	—	mΩ
Rss(ON)2	Static Source-Source On-Resistance 2	V _{DD} = 3.0V, I _D = 1A	_	120	-	mΩ
R _{SS(ON)2}	Static Source-Source On-Resistance 2	$V_{DD} = 2.5V, I_D = 500mA$	_	120)—	mΩ
V _{SD}	Diode Forward Voltage	V _{GS} = 0V I _S = 1A	_ •	0.75	1.0	V

Notes: 7. In case of Gate-Source voltage of charging MOSFET is 0V. In case of Gate-Source voltage of discharging MOSFET is 0V. 8. These specifications are guaranteed by design and will not be tested in production.



Application Information

Operation Mode

1. Normal Status

The AP9221 monitors the battery voltage and voltage difference between the VDD pin and VSS pin to control battery charging and discharging. The AP9221 will turn on discharging and charging MOSFET when the battery voltage is between the overdischarge detection voltage (V_{DL}) and overcharge detection voltage (V_{CU}), and the VM pin voltage is between the charge overcurrent detection voltage (V_{COC}) and discharge overcurrent detection voltage (V_{DOC}). In these conditions, the battery can charge and discharge freely. The R_{VMD} also does not connect to the VDD pin. In this status, the R_{VMS} does not connect to VSS pin.

2. Overcharge Status

If the battery voltage is more than V_{CU} during charging status for the overcharge detection delay time (tcu) or longer, the AP9221 turns off the charging MOSFET to stop charging. RvMD and RvMs are not connected in overcharge status.

When VM pin voltage is lower than V_{DOC} and battery voltage falls below V_{CL} , the AP9221 will release from overcharge status. When VM pin voltage is equal or more than V_{DOC} and battery voltage falls below V_{CU} , the AP9221 will release from overcharge status.

3. Overdischarge Status

If the battery voltage is less than V_{DL} during discharging status for the overdischarge detection delay time (t_{DL}) or longer, the AP9221 turns off the discharging MOSFET to stop discharging. In overdischarge status, the R_{VMD} is connected to the VDD, and VM pin voltage is pulled up to V_{DD} by R_{VMD} (but R_{VMS} is not connected). For the power-down mode version, the AP9221 recovers into normal status from overdischarge status only by charging the battery through the charger.

When VM pin voltage to VSS pin voltage is less than the typical -0.7V and the battery voltage rises over V_{DL} , the AP9221 will release from overdischarge status. If VM pin voltage to VSS pin voltage is higher than the typical -0.7V, the AP9221 will release from overdischarge status until the battery voltage rises over V_{DU} .

For auto-wake-up version DIODES[™] AP9221SA, the device recovers into normal status from overdischarge status if either of these two conditions are satisfied:

If a charger is connected: the AP9221SA overdischarge status is released in the same way as described above in "AP9221S Overdischarge Status" section.

If no charger is connected:

1) the battery voltage reaches the overdischarge release voltage (V_{DU}) or higher;

2) it maintains continuous time more than overdischarge release delay time tDLR.

4. Discharge Overcurrent and Short Current Status

If the battery is in discharge overcurrent status, the voltage of the VM pin to VSS pin is equal or more than V_{DOC} to V_{SHORT}, and detection lasts for the discharge overcurrent detection delay time (t_{DOC}) or longer, the AP9221 turns off the discharging MOSFET to stop discharging.

If the battery is in short current status, the voltage of the VM pin to VSS pin is equal to or more than V_{SHORT}, and the detection lasts for the short current detection delay time or longer, the AP9221 turns off the discharge MOSFET to stop discharging.

In discharge overcurrent or short current status, R_{VMS} is connected to V_{SS} , but R_{VMD} is not connected. The voltage of VM pin is almost equal to V_{DD} as long as the load is connected. When the load is disconnected, the voltage of VM pin will become almost equal to V_{SS} (due to R_{VMS} being connected) and then the AP9221 will release from discharge overcurrent or short current status.

5. Charge Overcurrent Status

If the battery is in charge current status, the voltage of the VM pin to VSS pin is equal to or less than V_{COC} , and the detection continues for the charge overcurrent detection delay time (t_{COC}) or longer, the AP9221 turns off the charging MOSFET to stop charging.



Application Information (continued)

6. 0V Battery Charging Function (Option)

This function is available as an option and can be factory set internally. The AP9221 has this function built-in.

0V charging function permits the charger to recharge the battery when its voltage is 0V due to self-discharge. If the 0V charging function is not present, the device will prevent the charger from recharging the battery when its voltage is 0V due to self-discharge.

(If a device without 0V charging function is needed, please contact the Diodes Incorporated sales team.)

7. Overvoltage Charger Detection Circuit

This function is used to monitor the charger voltage between the VDD pin and VM pin. When this voltage exceeds overvoltage charger detection voltage (8.0V Typ.), the AP9221 will turn off the charging MOSFET. When this voltage drops below overvoltage charger release voltage (7.3V Typ.), it then turns on the charging MOSFET. There are no delay times set for the detection and release.

8. Power-Down Mode or Auto-Wake-Up Function Option

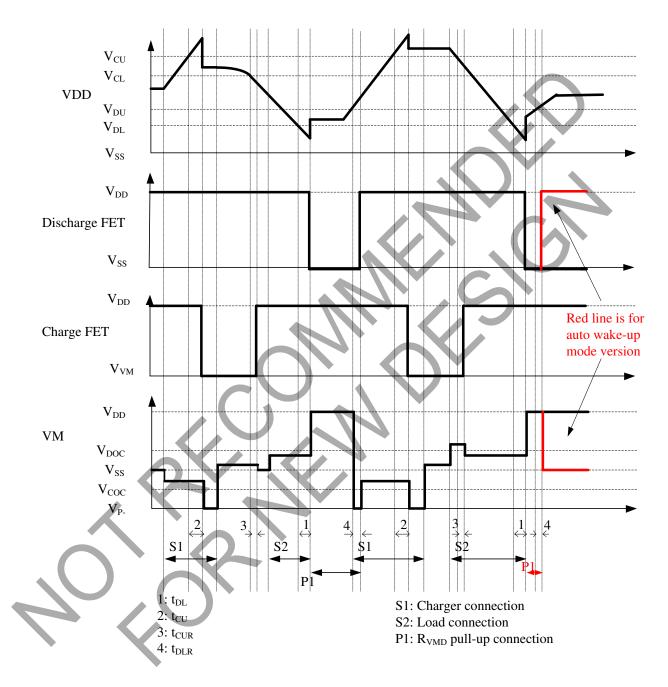
In a device with a power-down function, the device enters the overdischarge status during power-down mode. The IC enters sleep mode and the current consumption becomes very low, typically 0.1µA. To release from power-down status to the normal status, charger connection is required.

In a device with auto-wakeup mode, the IC remains active in the overdischarge state. The IC is released into the normal state by any operation that increases the battery voltage more than the overdischarge release voltage.



Application Information (Timing Chart)

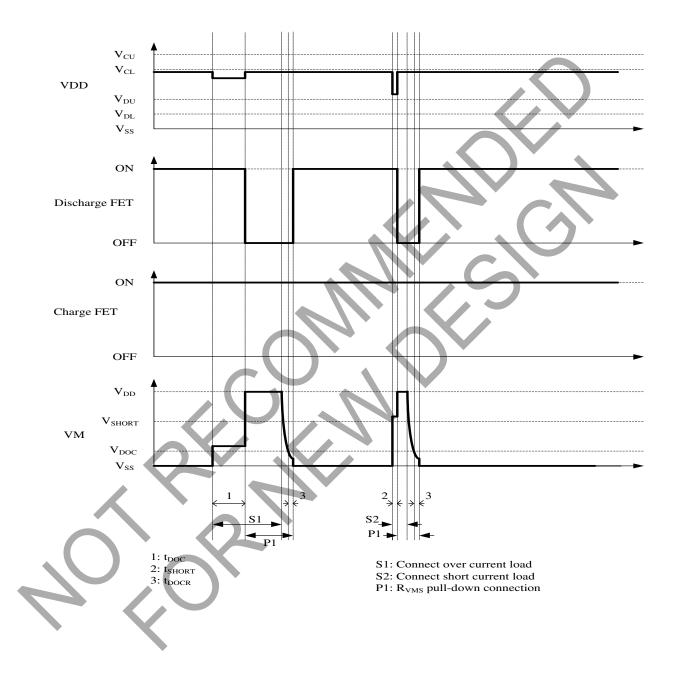
1. Overcharge and Overdischarge Detection





Application Information (Timing Chart) (continued)

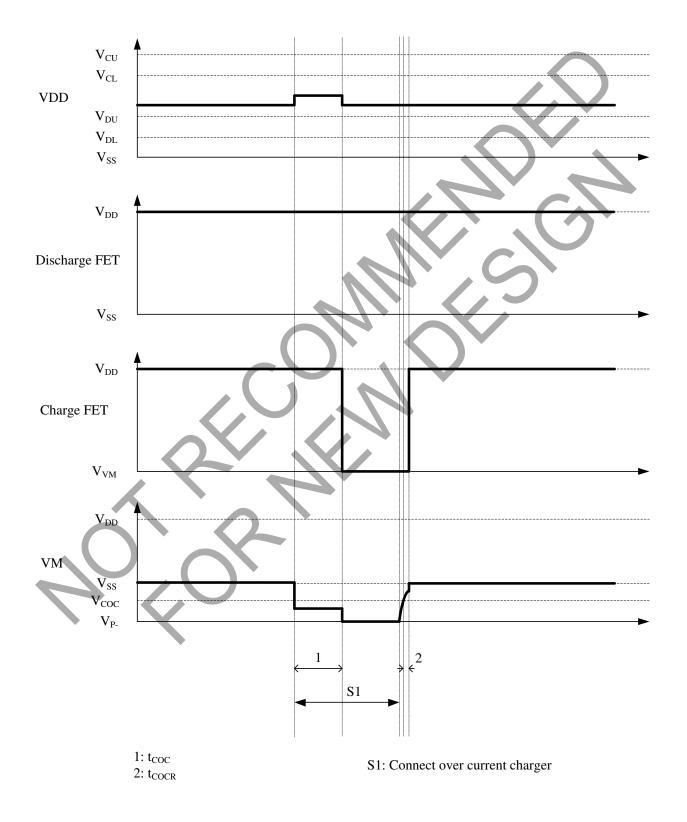
2. Discharge Overcurrent Detection





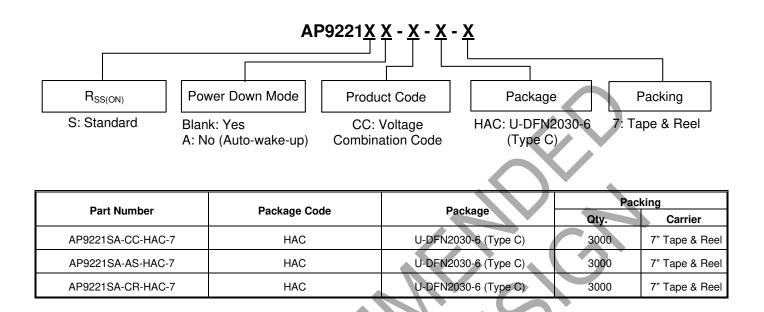
Application Information (Timing Chart) (continued)

3. Charge Overcurrent Detection





Ordering Information



Voltage Combination (Note 9)

Part Number	Overcharge Detection Voltage Vcu (V)	Overcharge Release Voltage V _{CL} (V)	Over- discharge Detection Voltage V _{DL} (V)	Over- discharge Release Voltage Vou (V)	Discharge Overcurrent Detection Voltage Vpoc (V)	Load Short Detection Voltage Vshort (V)	Charge Overcurrent Detection Voltage Vcoc (V)	Overvoltage Charge Detection Voltage Vovснg (V)	Overvoltage Charge Release Voltage VovcHGR (V)	Power- Down Function	Overcharge Protection Mode	0V Battery Charge Function
AP9221SA-CC-HAC- 7	4.200	4.000	2.750	2.950	0.055	0.276	-0.113	8.0	7.3	Auto Wake-up	Auto Release	Prohibition
AP9221SA-AS-HAC- 7	4.275	4.175	2.850	2.970	0.025	0.120	-0.020	8.0	7.3	Auto Wake-up	Auto Release	Prohibition
AP9221SA-CR-HAC- 7	4.370	4.220	2.800	3.000	0.130	0.350	-0.130	8.0	7.3	Auto Wake-up	Auto Release	Prohibition

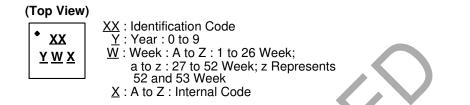
Note: 9. If any other voltage version options are needed, please contact the local sales office.

The AP9221 Delay Time Combination

Part Number	Overcharge Detection Delay Time tCU	Overcharge Release Delay Time tCUR	Overdischarge Detection Delay Time tDL	Overdischarge Release Delay Time tDLR	Discharge Overcurrent Detection Delay Time tDOC	Discharge Overcurrent Release Delay Time tDOCR	Charge Overcurrent Detection Delay Time tcoc	Charge Overcurrent Release Delay Time tCOCR	Load Short Detection Delay Time tSHORT
AP9221SX-XX-HAC-7	1.0s	2.0ms	115ms	2.0ms	10.0ms	2.0ms	10.0ms	2.0ms	360µs



Marking Information

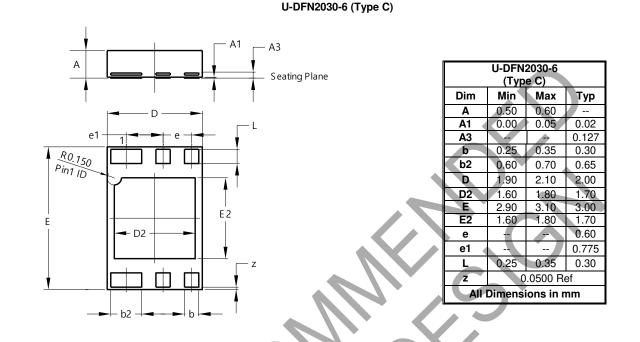


Part Number	Package	Identification Code
AP9221SA-CC-HAC-7	U-DFN2030-6 (Type C)	20
AP9221SA-AS-HAC-7	U-DFN2030-6 (Type C)	2D
AP9221SA-CR-HAC-7	U-DFN2030-6 (Type C)	2E



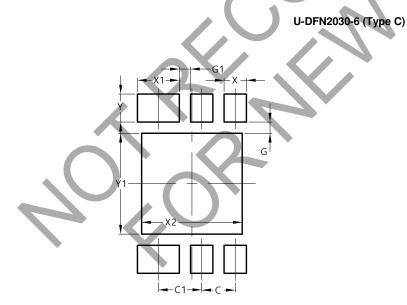
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.600
C1	0.775
G	0.200
G1	0.200
Х	0.400
X1	0.750
X2	1.800
Ŷ	0.500
Y1	1.800

Mechanical Data

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe Solderable per MIL-STD-202, Method 208 4
- Weight: 0.011 grams (Approximate)



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